FEATURES

- Maximum Gate Trigger Current: 2, 20 or 200μA
- Tight Gate Trigger Voltage Range: .44 to .6V
- Voltage Ratings: to 400V
- . Specified for dv/dt and Switching Time

DESCRIPTION

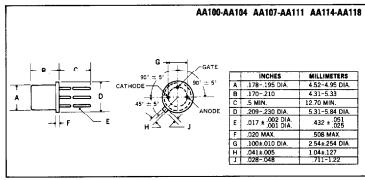
This data sheet describes Microsemi's AA Series 0.5A SCRs designed for low-current sensing applications. Units are available in a complete range of blocking voltages from 60 to 400 volts

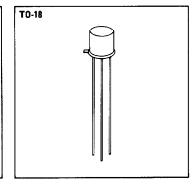
The AA100 series offers a maximum gate trigger current of 2.0 microamps making it the most sensitive device of its type. The AA107 series has a maximum I_{QT} of $20\mu A$ while this parameter is specified at $200\mu A$ for the AA114 series.

ABSOLUTE MAXIMUM RATINGS

ADDED I III/AMIONI NATITAD	AA106 AA107	AA101 AA108	AA102 AA108	AA103 AA110	AA104 AA111
	AA114	AA115	AA116	AA117	AA118
Repetitive Peak Off-State Voltage, VDRM	60V	100V	200V	300V	400V
Repetitive Peak Reverse Voltage, V	60V	100V	200V	300V	400V
Non-Repetitive Peak Reverse Voltage, V _{RSM}	80V	150V	300V	400V	500V
Non-Repetitive Peak Off-State Voltage, VDSM					
D.C. On-State Current, I _T					
75°C Ambient			250mA	,	
100°C Case			500mA		
Repetitive Peak On-State Current, I _{TRM} Peak One Cycle Surge (Non-Rep.) On-State Curr			up to 30A		
Peak One Cycle Surge (Non-Rep.) On-State Curr	ent, I _{TSM}	.,,	5A	,	
Peak Gate Current, I			250mA		
Average Gate Current, In			25mA		
Reverse Gate Voltage V _{GR}			6V		
Operating and Storage Temperature Range			65°C to +150°C		

MECHANICAL SPECIFICATIONS

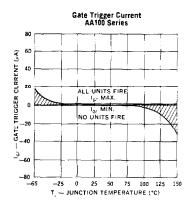


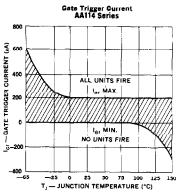


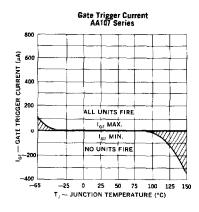


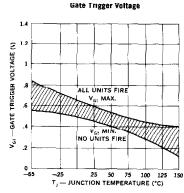
Parameter	Symbol	Min.	Typical	Max.	Units	Test Conditions
SUBGROUP 1						
Visual & Mechanical		L <u>-</u>				
SUBGROUP 2 (25°C TESTS)						
Off-State Current	IDRM	-	.01	0.1	μА	$R_{GK} = 1K$, $V_{DRM} = Rating$
Reverse Current	IKKM		.01	0.1	μΛ.	R _{GK} = 1K, V _{RRM} = Rating
Reverse Gate Current	I _{GR}	l —	0.1	0.2	μA	$V_{GR} = 2V$
Gate Trigger Current	IGT	}				$R_{65} = 10K, V_{D} = 5V$
AA100-104		í —	0.2	2.0	μA	
AA107-111			2.0	20	μA	
AA114-118		-	20	200	μA	
Gate Trigger Voltage	V _{GT}	0.44	0.52	0.60	ν	$R_{css} = 100\Omega$, $V_{b} = 5V$
On-State Voltage	ν _τ	_	1.1	1.5	٧	$I_{\tau} = 1.0 \text{ A (pulse)}$
Holding Current	_ 1 _H	0.3	0.5	2.0	mA	R _{GK} = 1K
SUBGROUP 3 (25°C TESTS)						
Off-State Voltage — Critical Rate of Rise	dv/dt	50	100	_	V/μs	$R_{GK} = 1K, V_D \approx 30V$
Gate Trigger — on Pulse Width	t _{pq} (on)	i —	0.5	2.0	μS	$I_c = 10$ mA, $I_T = 1$ A, $V_D = 30$ V
Delay Time	t _d	l —	0.6		μS	$I_{\rm G} = 10 {\rm mA}, I_{\rm T} = 1 {\rm A}, V_{\rm D} = 30 {\rm V}$
Rise Time	t,	_	0.4	l —	μS	$I_0 = 10 \text{mA}, I_T = 1 \text{A}, V_0 = 30 \text{V}$
Circuit Commutated Turn-off Time	t _r t _q	<u> </u>	20	50	μS	$I_{\rm T} = 1$ A, $I_{\rm R} = 1$ A, $R_{\rm GK} = 1$ K
SUBGROUP 4 (125°C TESTS)						
Off-State Current	IDRM	_	10	20	μA	$R_{GK} = 1K$, $V_{DRM} = Rating$
Reverse Current	IRRM	i —	30	100	μА	$R_{GK} = 1K, V_{RRM} = Rating$
Gate Trigger Voltage	V _{GT}	0.15	0.2		V	$R_{GS} = 100\Omega, V_D = 5V$
Holding Current	I _H	0.2	0.4	1.5	mA	$R_{\Theta K} = 1K$

Note: Blocking voltage ratings apply over the full operating temperature range, provided the gate is connected to the cathode through a resistor, 1000 ohms or smaller, or other adequate bias is used.





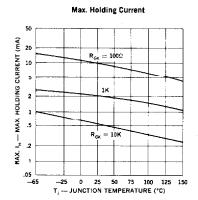


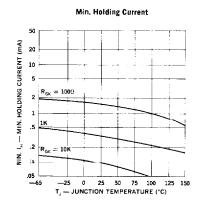


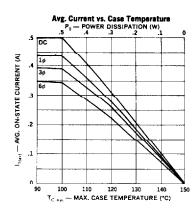
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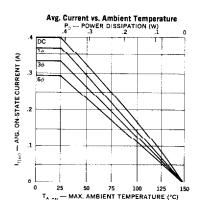
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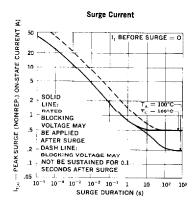
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